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## BIB DATA SHEET

CONFIRMATION NO. 7107

<b>SERIAL NUMBER</b> 10/527,642	<b>FILING or 371(c) DATE</b> 03/14/2005 <b>RULE</b>	<b>CLASS</b> 438	<b>GROUP ART UNIT</b> 2812	<b>ATTORNEY DOCKET NO.</b> 267410US26PCT		
<b>APPLICANTS</b> Masanobu Igeta, Yamanashi, JAPAN; Shintaro Aoyama, Yamanashi, JAPAN; <i>CL</i> Hiroshi Shinriki, Chiba, JAPAN;						
<b>** CONTINUING DATA *****</b> This application is a 371 of PCT/JP03/11971 09/19/2003 <i>CL</i>						
<b>** FOREIGN APPLICATIONS *****</b> JAPAN 2002=273709 09/19/2002 <i>CL</i>						
<b>** IF REQUIRED, FOREIGN FILING LICENSE GRANTED **</b>						
Foreign Priority claimed <input checked="" type="checkbox"/> Yes <input type="checkbox"/> No 35 USC 119(a-d) conditions met <input checked="" type="checkbox"/> Yes <input type="checkbox"/> No Verified and Acknowledged <u>/CHEUNG LEE/</u> Examiner's Signature		<input type="checkbox"/> Met after Allowance Initials	<b>STATE OR COUNTRY</b> JAPAN	<b>SHEETS DRAWINGS</b> 15	<b>TOTAL CLAIMS</b> 20	<b>INDEPENDENT CLAIMS</b> 5
<b>ADDRESS</b> OBLON, SPIVAK, MCCLELLAND MAIER & NEUSTADT, P.C. 1940 DUKE STREET ALEXANDRIA, VA 22314 UNITED STATES						
<b>TITLE</b> Method for forming insulating film on substrate, method for manufacturing semiconductor device and substrate-processing apparatus						
<b>FILING FEE RECEIVED</b> 1910	FEES: Authority has been given in Paper No. _____ to charge/credit DEPOSIT ACCOUNT No. _____ for following:			<input type="checkbox"/> All Fees <input type="checkbox"/> 1.16 Fees (Filing) <input type="checkbox"/> 1.17 Fees (Processing Ext. of time) <input type="checkbox"/> 1.18 Fees (Issue) <input type="checkbox"/> Other _____ <input type="checkbox"/> Credit		